

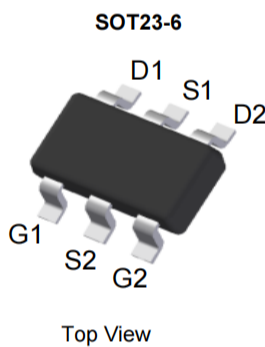
**Product Summary**

- $V_{DS} = 30V, I_D = 4A$
- $R_{DS(ON)} < 75m\Omega @ V_{GS}=4.5V$
- $R_{DS(ON)} < 45m\Omega @ V_{GS}=10V$

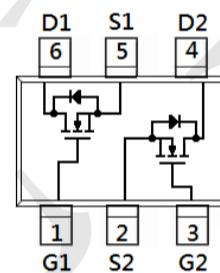
**Application**

- *Notebook*
- *Load Switch*
- *Networking*
- *Hand-held Instruments*

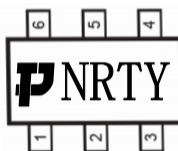
**Package and Pin Configuration**



**Circuit diagram**



**Marking:**



**Absolute Maximum Ratings ( $T_A=25^\circ C$  unless otherwise noted)**

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	4	A
Drain Current-Pulsed <sup>(Note 1)</sup>	$I_{DM}$	20	A
Maximum Power Dissipation	$P_D$	1.2	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

**Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	104	$^\circ C/W$
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**Electrical Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	30			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=30V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	1.5	2.2	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=3A$	-	35	45	$m\Omega$
		$V_{GS}=4.5V, I_D=2A$	-	60	75	$m\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=3.5A$	-	12	-	S
<b>Dynamic Characteristics</b> (Note 4)						
Input Capacitance	$C_{iss}$	$V_{DS}=15V, V_{GS}=0V,$ $F=1.0MHz$	-	170	-	PF
Output Capacitance	$C_{oss}$		-	35	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	23	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS}=15V, R_L=4.2\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	4.5	-	nS
Turn-on Rise Time	$t_r$		-	1.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	18.5	-	nS
Turn-Off Fall Time	$t_f$		-	15.5	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=15V, I_D=3.5A,$ $V_{GS}=10V$	-	4.0	-	nC
Gate-Source Charge	$Q_{gs}$		-	0.75	-	nC
Gate-Drain Charge	$Q_{gd}$		-	0.65	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=3.5A$	-	0.8	1.2	V
Diode Forward Current (Note 2)	$I_S$		-	-	3.5	A

Typical Electrical and Thermal Characteristics

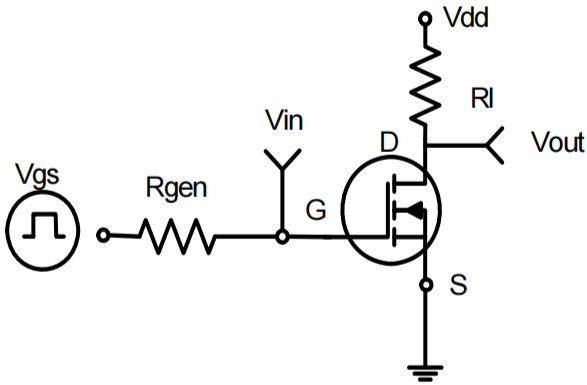


Figure 1: Switching Test Circuit

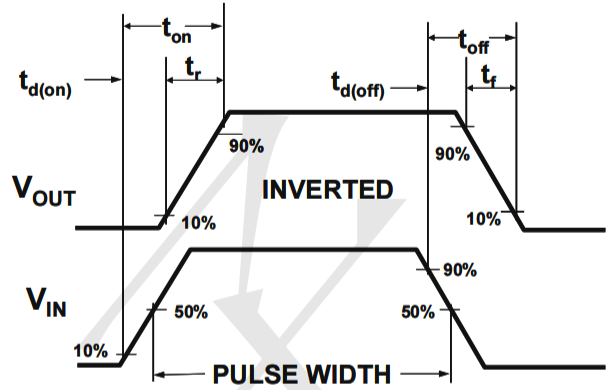
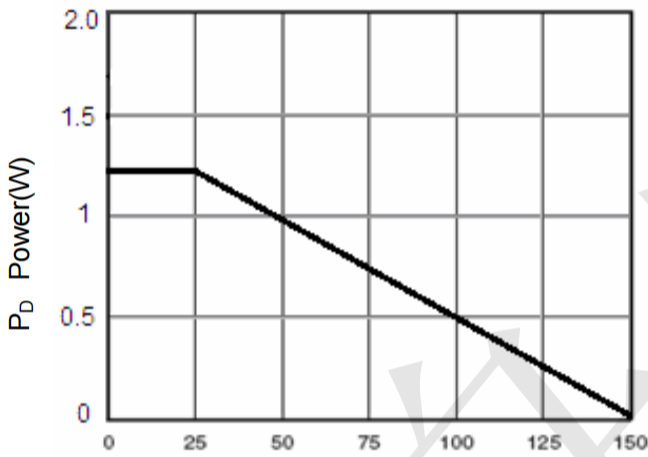
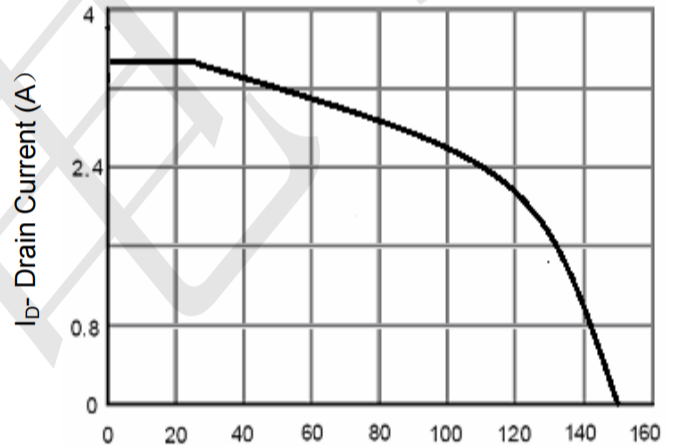


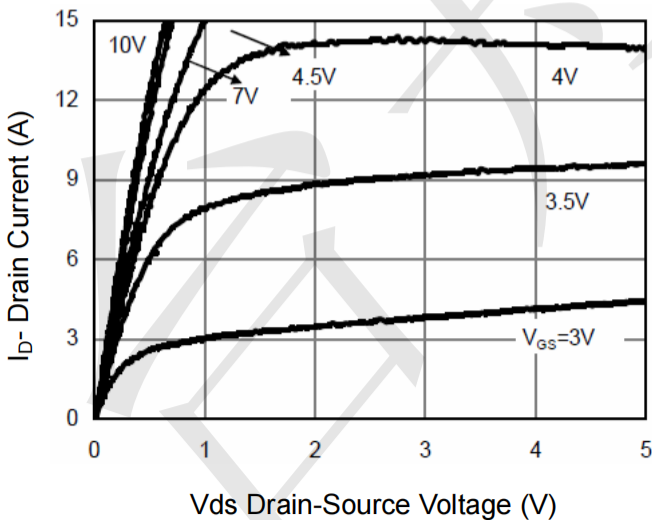
Figure 2: Switching Waveforms



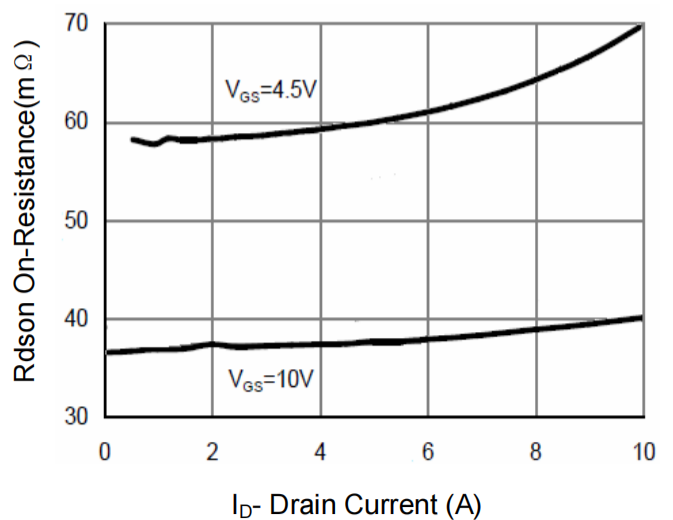
T<sub>J</sub>-Junction Temperature(°C)  
Figure 3 Power Dissipation



T<sub>J</sub>-Junction Temperature(°C)  
Figure 4 Drain Current



V<sub>ds</sub> Drain-Source Voltage (V)  
Figure 5 Output Characteristics



Id- Drain Current (A)  
Figure 6 Drain-Source On-Resistance

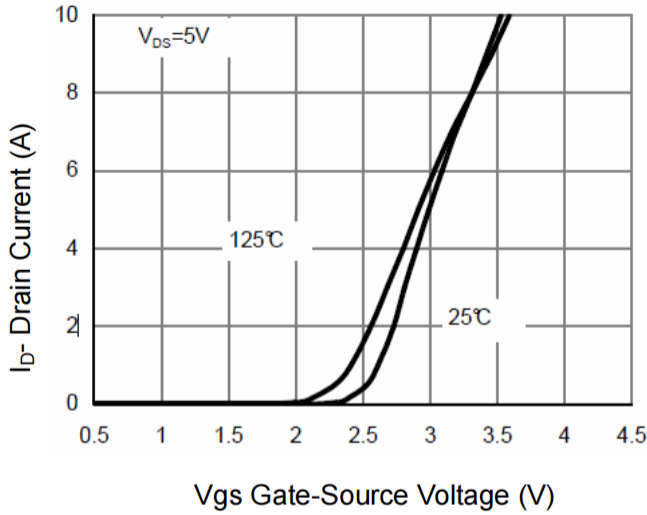


Figure 7 Transfer Characteristics

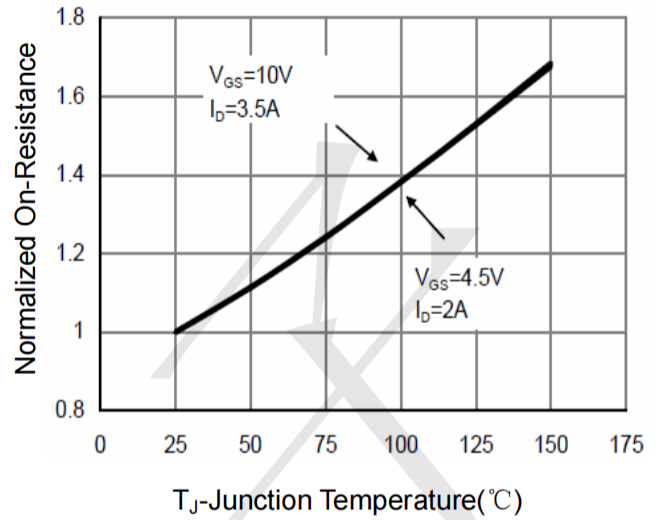


Figure 8 Drain-Source On-Resistance

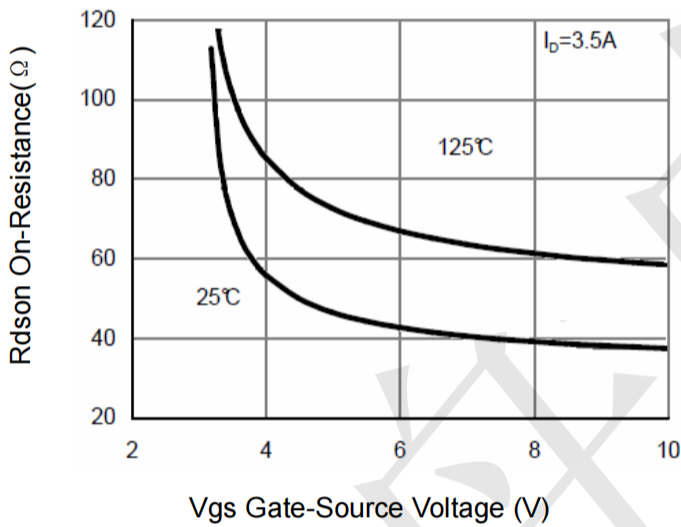


Figure 9  $R_{DS(on)}$  vs  $V_{GS}$

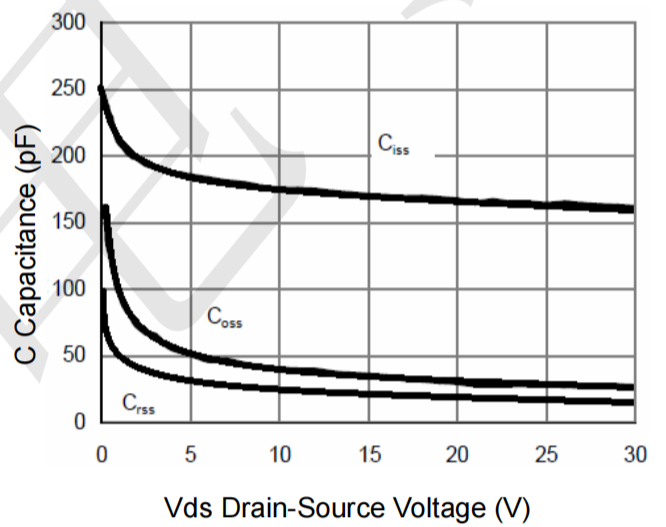


Figure 10 Capacitance vs  $V_{DS}$

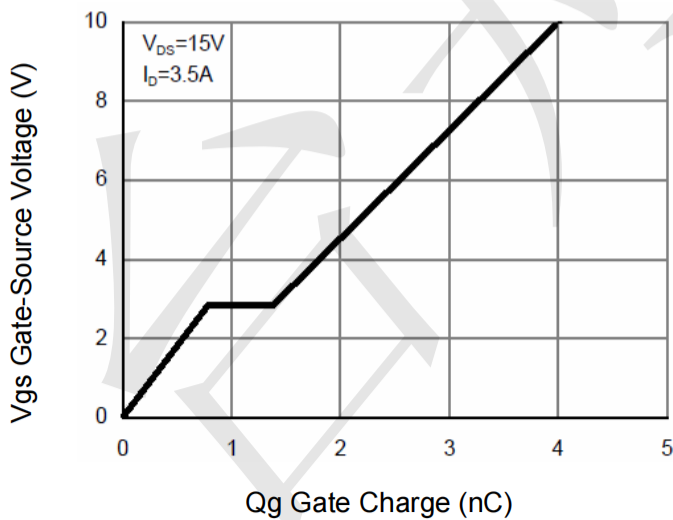


Figure 11 Gate Charge

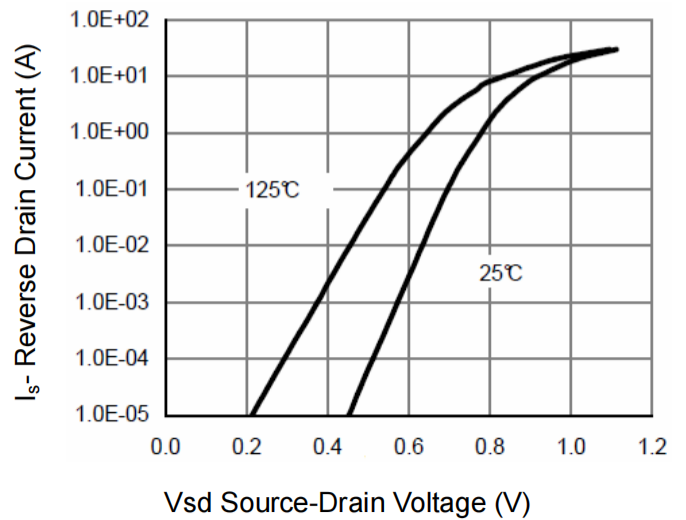
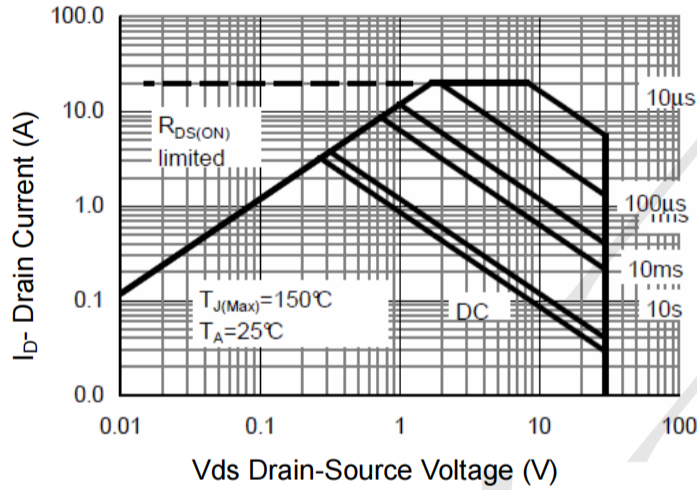
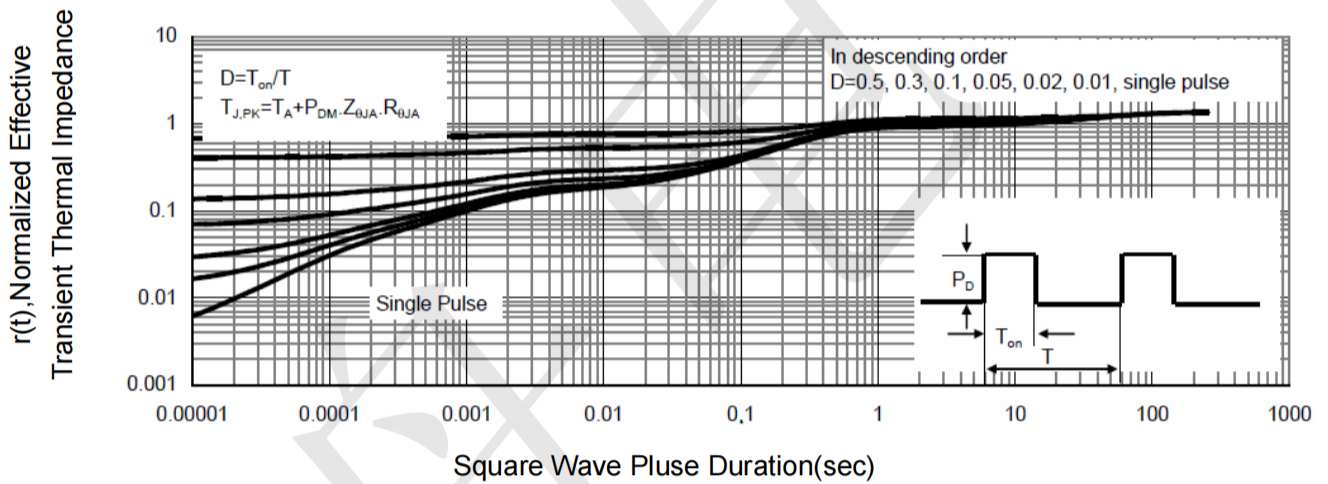


Figure 12 Source- Drain Diode Forward



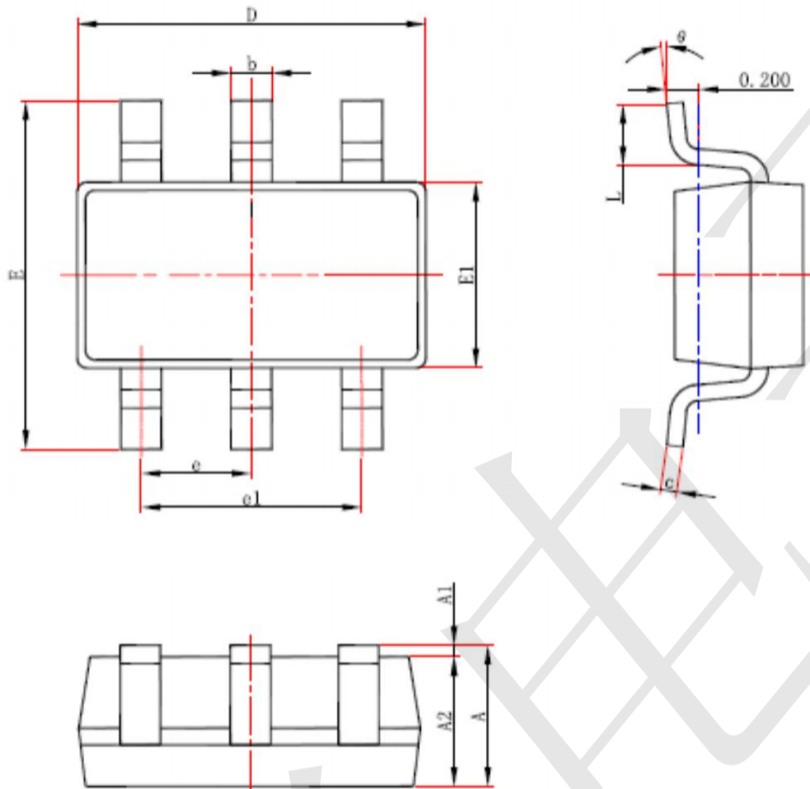
**Figure 13 Safe Operation Area**



**Figure 14 Normalized Maximum Transient Thermal Impedance**



**SOT23-6 Package Outline Dimensions**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°